L Number	Hits	Search Text	DB	Time stamp
1	467577	integrated near circuit	USPAT;	2004/06/18 07:13
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
2	355	(porous same (silica silicate silicalite)) and (((binder) same	USPAT;	2004/06/18 07:45
		(radiation photosensitive ultraviolet)))	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
3	4	(integrated near circuit) and ((porous same (silica silicate	USPAT;	2004/06/18 07:14
		silicalite)) and (((binder) same (radiation photosensitive	US-PGPUB;	
		ultraviolet))))	EPO; JPO;	
			DERWENT	
4	76	(porous near (silica silicate silicalite (silicon near dioxide)	USPAT;	2004/06/18 07:46
		sio?sub.2)) and (((binder) same (radiation photosensitive	US-PGPUB;	
		ultraviolet)))	EPO; JPO;	
			DERWENT	
5	2	(integrated near circuit) and ((porous near (silica silicate	USPAT;	2004/06/18 07:46
		silicalite (silicon near dioxide) sio?sub.2)) and (((binder) same	US-PGPUB;	
		(radiation photosensitive ultraviolet))))	EPO; JPO;	
		, , , , , , , , , , , , , , , , , , , ,	DERWENT	
6	0	((integrated near circuit) and ((porous near (silica silicate	USPAT;	2004/06/18 07:51
		silicalite (silicon near dioxide) sio?sub.2)) and (((binder) same	US-PGPUB:	
		(radiation photosensitive ultraviolet))))) not ((integrated near	EPO; JPO;	
		circuit) and ((porous same (silica silicate silicalite)) and	DERWENT	
		(((binder) same (radiation photosensitive ultraviolet)))))	DERWEIT	
7	34917	(integrated near circuit) and (metal near layer)	USPAT;	2004/06/18 07:51
		(modification)	US-PGPUB;	2004/00/10 07:51
			EPO; JPO;	
			DERWENT	
8	17576	((integrated near circuit) and (metal near layer)) and wafer	USPAT;	2004/06/18 08:00
		((integral of the content of the con	US-PGPUB;	200-100/10 00:00
			EPO; JPO;	
			DERWENT	
9	8079	(((integrated near circuit) and (metal near layer)) and wafer)	USPAT;	2004/06/18 08:00
		and (dielectric near layer)	US-PGPUB:	2004/00/10 00:00
		and (anotoento troat rayor)	EPO; JPO;	
			DERWENT	
10	1045	(((((integrated near circuit) and (metal near layer)) and wafer)	USPAT;	2004/06/18 08:00
	1010	and (dielectric near layer)) and silica	US-PGPUB;	2004/00/16 06:00
		and (anotocario rioda layor)) and office	EPO; JPO;	
			DERWENT	
11	6563	((integrated near circuit) and (metal near layer)) and (silicon	USPAT;	2004/06/18 08:00
	0000	near wafer)	US-PGPUB;	2004/00/10 00:00
		Troui Watery	EPO; JPO;	
			DERWENT	
12	3025	(((integrated near circuit) and (metal near layer)) and (silicon		2004/06/49 00:00
	3020	near wafer)) and (dielectric near layer)	USPAT;	2004/06/18 08:00
		noar matery, and (dielectric fieal layer)	US-PGPUB;	
ļ			EPO; JPO;	
13	7	((((integrated near circuit) and (motal near layer)) and (allies	DERWENT	2004/00/40 00 01
	'	((((integrated near circuit) and (metal near layer)) and (silicon near wafer)) and (dielectric near layer)) and	USPAT;	2004/06/18 08:01
		252/570;524/588;522/99,148;528/32.ccls.	US-PGPUB;	
		232131 0,3241300,322188, 140,328132.CCIS.	EPO; JPO;	
			DERWENT	